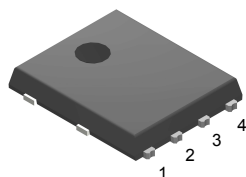
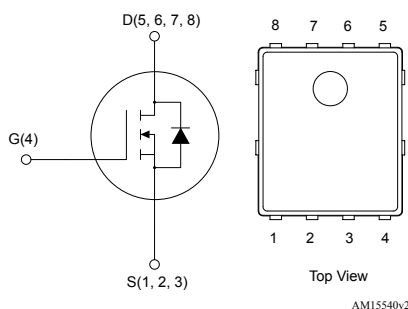


Automotive N-channel enhancement mode logic level 40 V, 0.75 mΩ max., 373 A STripFET F8 Power MOSFET in a PowerFLAT 5x6



PowerFLAT 5x6



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STL325N4LF8AG	40 V	0.75 mΩ	373 A

- AEC-Q101 qualified 
- MSL1 grade
- 175 °C operating temperature
- 100% avalanche tested
- Wettable flank package

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET F8 technology featuring an enhanced trench gate structure.

It ensures very low on-state resistance while reducing internal capacitances and gate charge for faster and more efficient switching.



Product status link

[STL325N4LF8AG](#)

Product summary

Order code	STL325N4LF8AG
Marking	325N4LF8
Package	PowerFLAT 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings (at $T_C = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 16	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	373	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	264	
$I_{DM}^{(1)(2)(3)}$	Drain current (pulsed), $t_P = 10\text{ }\mu\text{s}$	1492	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	188	W
I_{AS}	Single pulse avalanche current (pulse width limited by T_J max.)	60	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$, $I_D = 60\text{ A}$, $R_{Gmin} = 25\text{ }\Omega$)	590	mJ
T_J	Operating junction temperature range	-55 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		

1. The value is relevant to R_{thJC} . Current limitations will come from the operative conditions, such as temperature and thermal resistance of the PCB.
2. Specified by design and evaluated by characterization, not tested in production.
3. Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJA}^{(1)}$	Thermal resistance, junction-to-ambient (on 2s2p FR-4 board vertical in still area)	20	$^{\circ}\text{C/W}$
R_{thJC}	Thermal resistance, junction-to-case	0.8	$^{\circ}\text{C/W}$

1. Defined according to JEDEC standards (JESD51-5, -7).

2 Electrical characteristics

$T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	40			V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125^{\circ}\text{C}$ ⁽¹⁾			100	
I_{GSS}	Gate-body leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.2		2.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$		0.55	0.75	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 60\text{ A}$		0.85	1.1	

1. Specified by design and evaluated by characterization, not tested in production.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} ⁽¹⁾	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	7657	-	pF
C_{oss} ⁽¹⁾	Output capacitance		-	1968	-	pF
C_{rss} ⁽¹⁾	Reverse transfer capacitance		-	50	-	pF
Q_g ⁽¹⁾	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 0\text{ to }4.5\text{ V}$	-	39	-	nC
		$V_{DD} = 20\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$	-	95	-	
Q_{gs} ⁽¹⁾	Gate-source charge	$V_{DD} = 20\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 0\text{ to }4.5\text{ V}$	-	23	-	nC
Q_{gd} ⁽¹⁾	Gate-drain charge		-	6	-	nC

1. Specified by design and evaluated by characterization, not tested in production.

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ ⁽¹⁾	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 60\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	12.5	-	ns
t_r ⁽¹⁾	Rise time		-	6.5	-	ns
$t_{d(off)}$ ⁽¹⁾	Turn-off delay time		-	89	-	ns
t_f ⁽¹⁾	Fall time		-	21	-	ns

1. Specified by design and evaluated by characterization, not tested in production.

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1) (2)}$	Forward on current (continuous)	$T_C = 25\text{ }^{\circ}\text{C}$	-		135	A
V_{SD}	Forward on voltage	$I_{SD} = 60\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.1	V
$t_{rr}^{(1)}$	Reverse recovery time	$I_D = 60\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 32\text{ V}$	-	60.1		ns
$Q_{rr}^{(1)}$	Reverse recovery charge		-	74.4		nC
$I_{RRM}^{(1)}$	Reverse recovery current		-	2.5		A

1. Specified by design and evaluated by characterization, not tested in production.
2. The value is relevant to R_{thJC} . Current limitations will come from the operating conditions, such as temperature and thermal resistance of the PCB.

2.1 Electrical characteristics (curves)

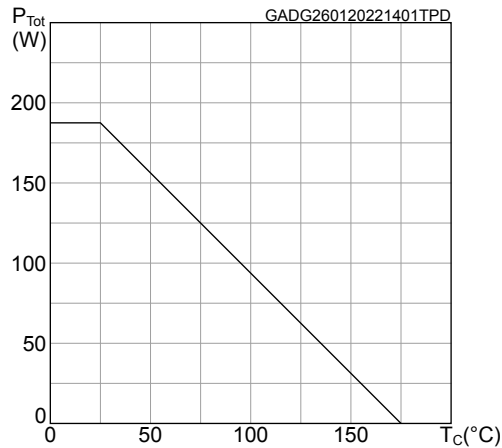
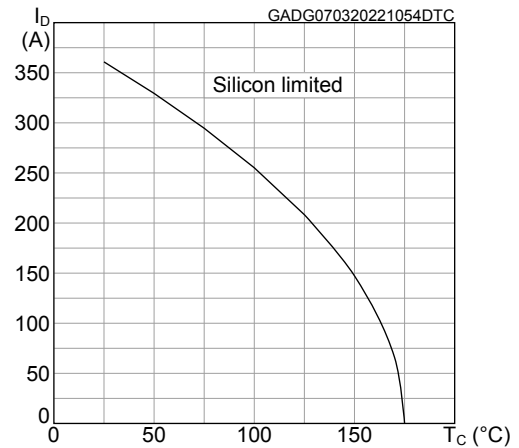
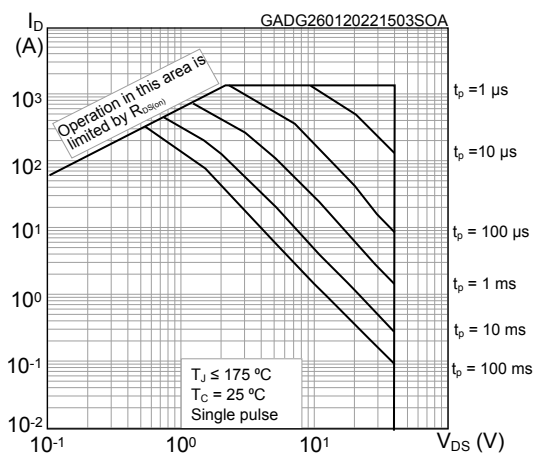
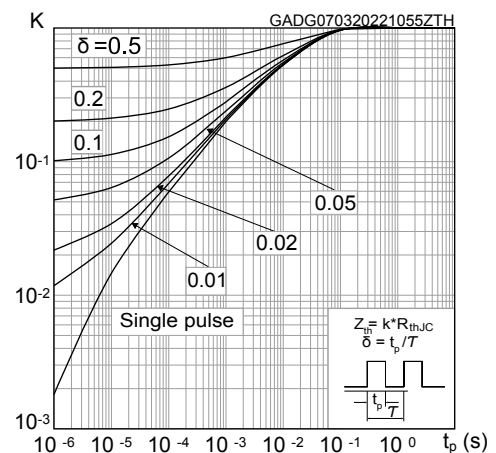
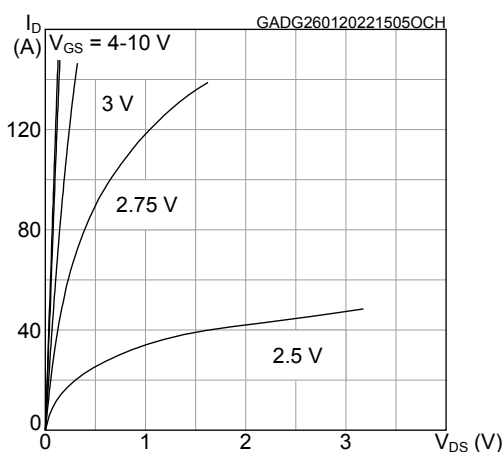
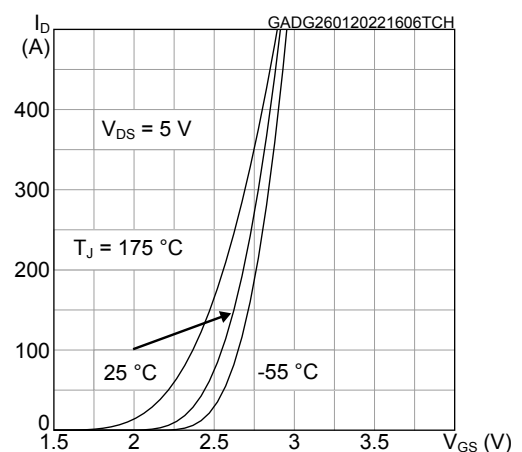
Figure 1. Total power dissipation

Figure 2. Drain current vs case temperature

Figure 3. Safe operating area

Figure 4. Normalized transient thermal impedance

Figure 5. Typical output characteristics

Figure 6. Typical transfer characteristics


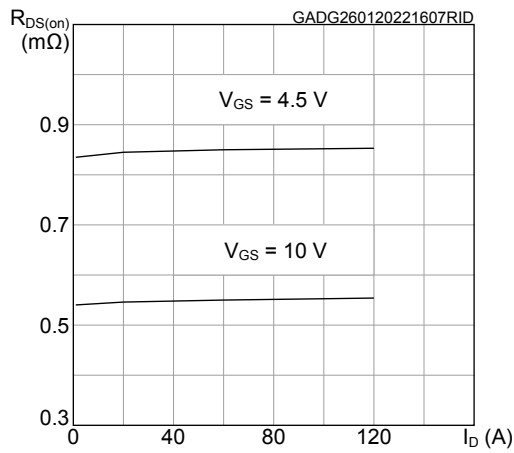
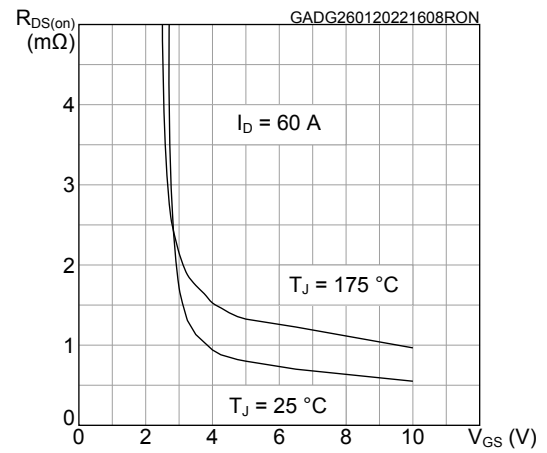
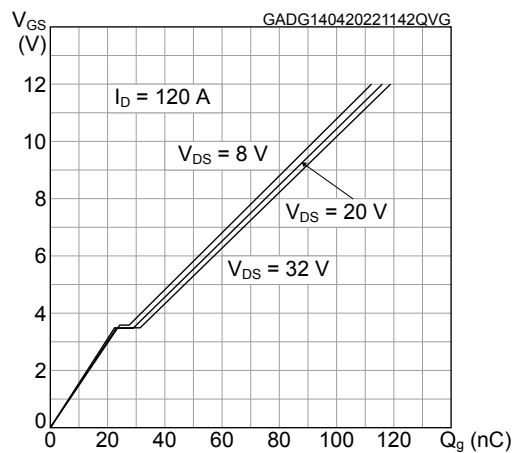
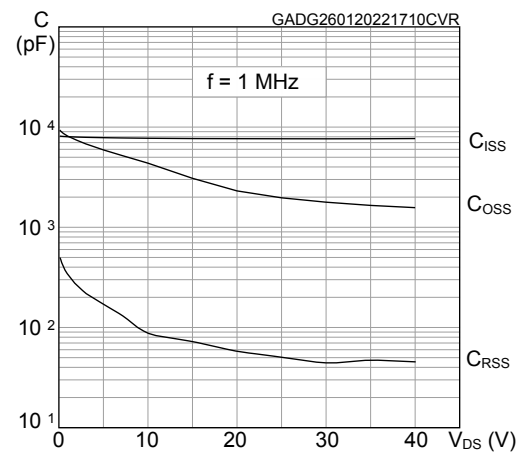
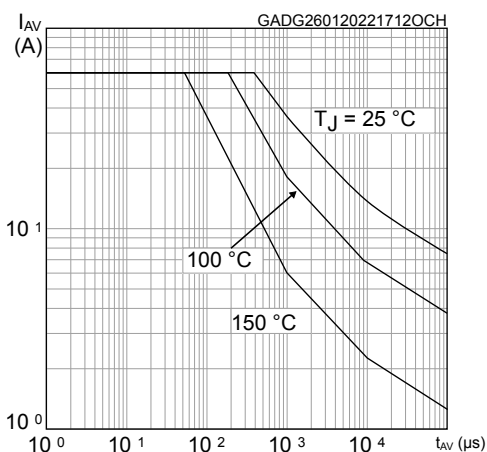
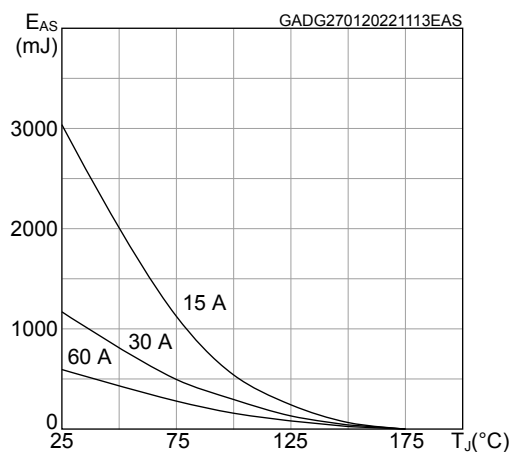
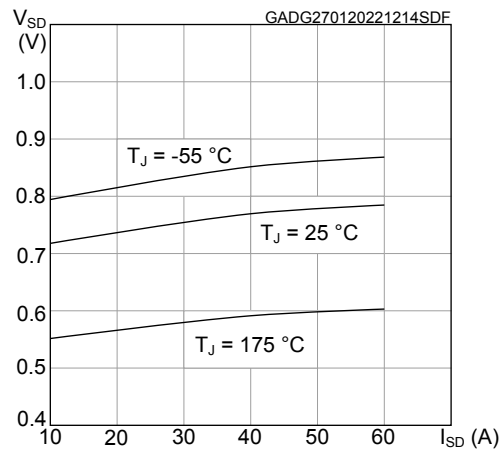
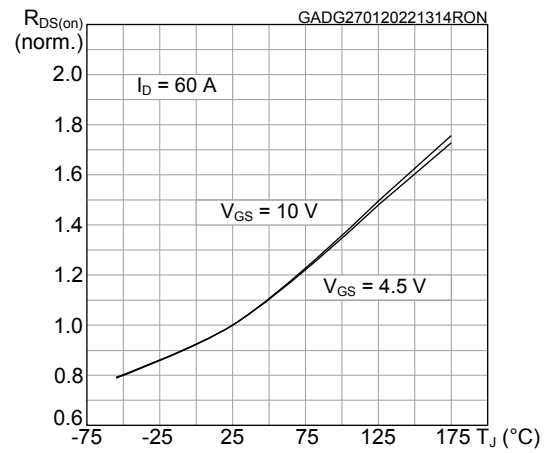
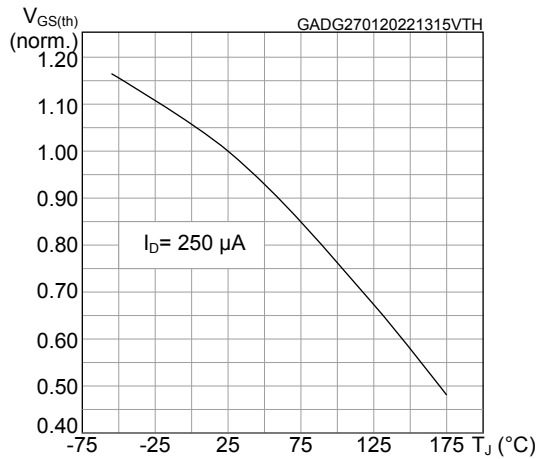
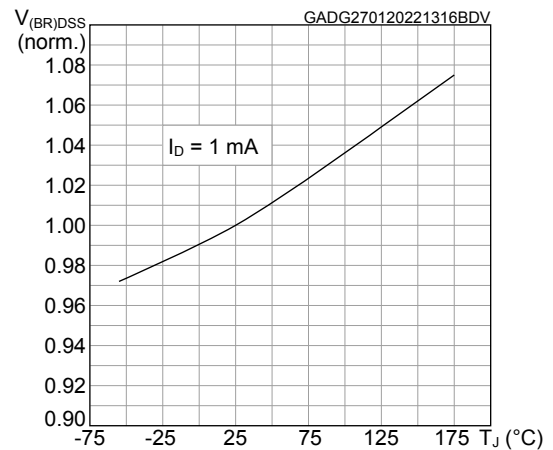
Figure 7. Typical drain-source on-resistance

Figure 8. Typical on-resistance vs gate-source voltage

Figure 9. Typical gate charge characteristics

Figure 10. Typical capacitance characteristics

Figure 11. Avalanche characteristics

Figure 12. Avalanche energy


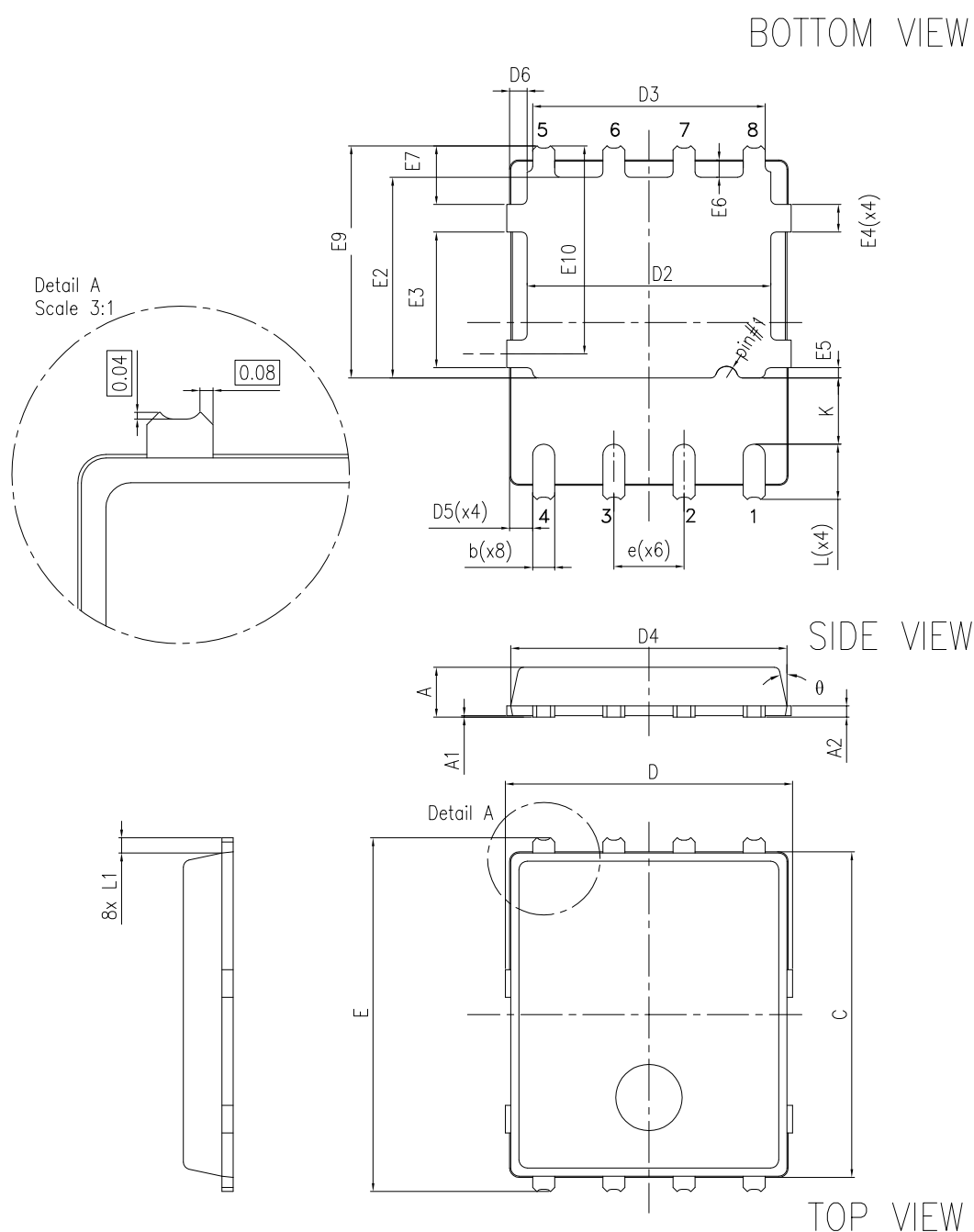
Figure 13. Typical reverse diode forward characteristics

Figure 14. Normalized on-resistance vs temperature

Figure 15. Normalized gate threshold voltage vs temperature

Figure 16. Normalized $V_{(BR)DSS}$ vs temperature


3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 PowerFLAT 5x6 WF type C package information

Figure 17. PowerFLAT 5x6 WF type C package outline

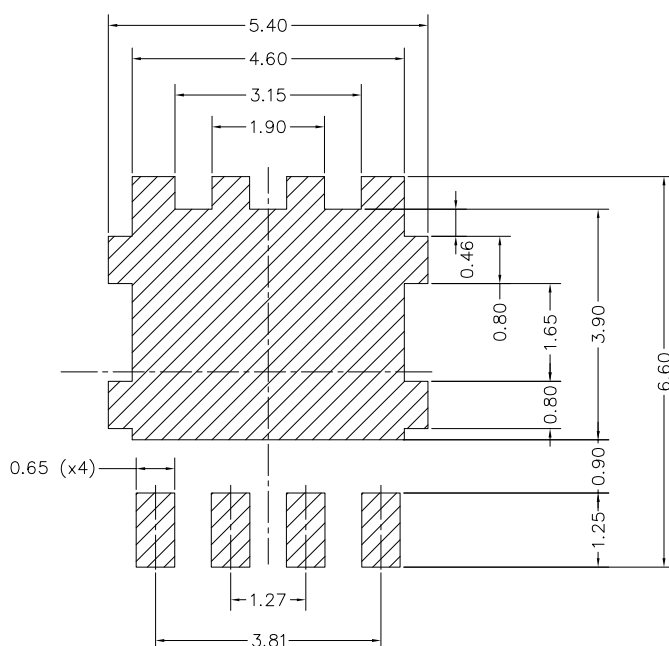


8231817_WF_typeC_r20

Table 7. PowerFLAT 5x6 WF type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.00		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.10
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.10
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.85	1.00	1.15
E9	4.00	4.20	4.40
E10	3.55	3.70	3.85
K	1.05		1.35
L	0.90	1.00	1.10
L1	0.175	0.275	0.375
θ	0°		12°

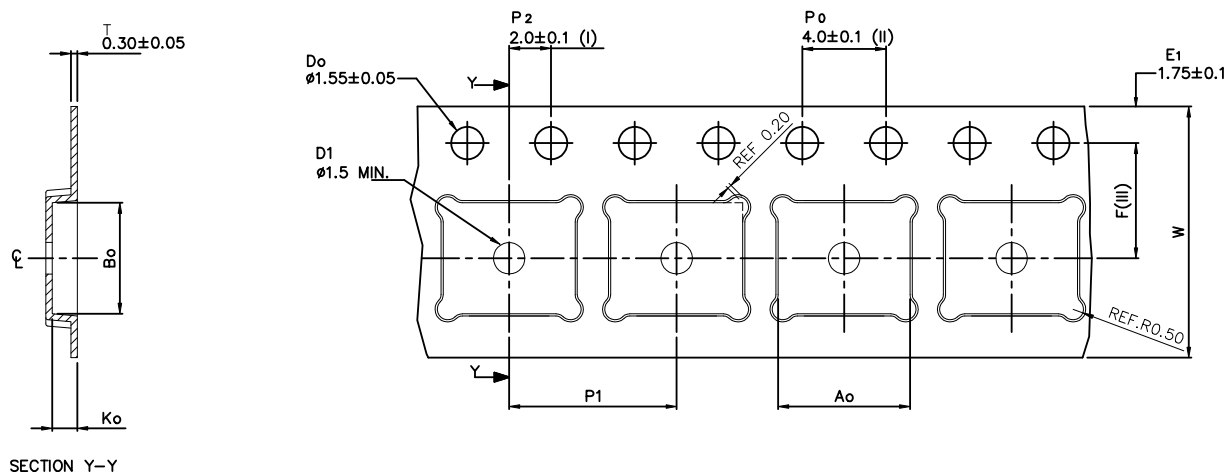
Figure 18. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817_FOOTPRINT_rev20

3.2 PowerFLAT 5x6 packing information

Figure 19. PowerFLAT 5x6 tape (dimensions are in mm)



Ao	6.30	+/-	0.1
Bo	5.30	+/-	0.1
Ko	1.20	+/-	0.1
F	5.50	+/-	0.1
P1	8.00	+/-	0.1
W	12.00	+/-	0.3

- (I) Measured from centreline of sprocket hole to centreline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .
- (III) Measured from centreline of sprocket hole to centreline of pocket

Base and bulk quantity 3000 pcs
All dimensions are in millimeters

8234350_Tape_rev_C

Figure 20. PowerFLAT 5x6 package orientation in carrier tape

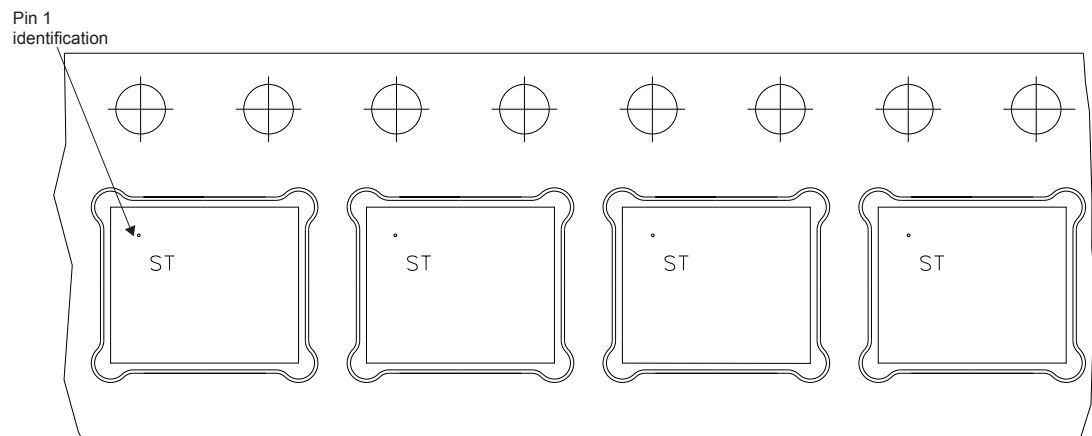
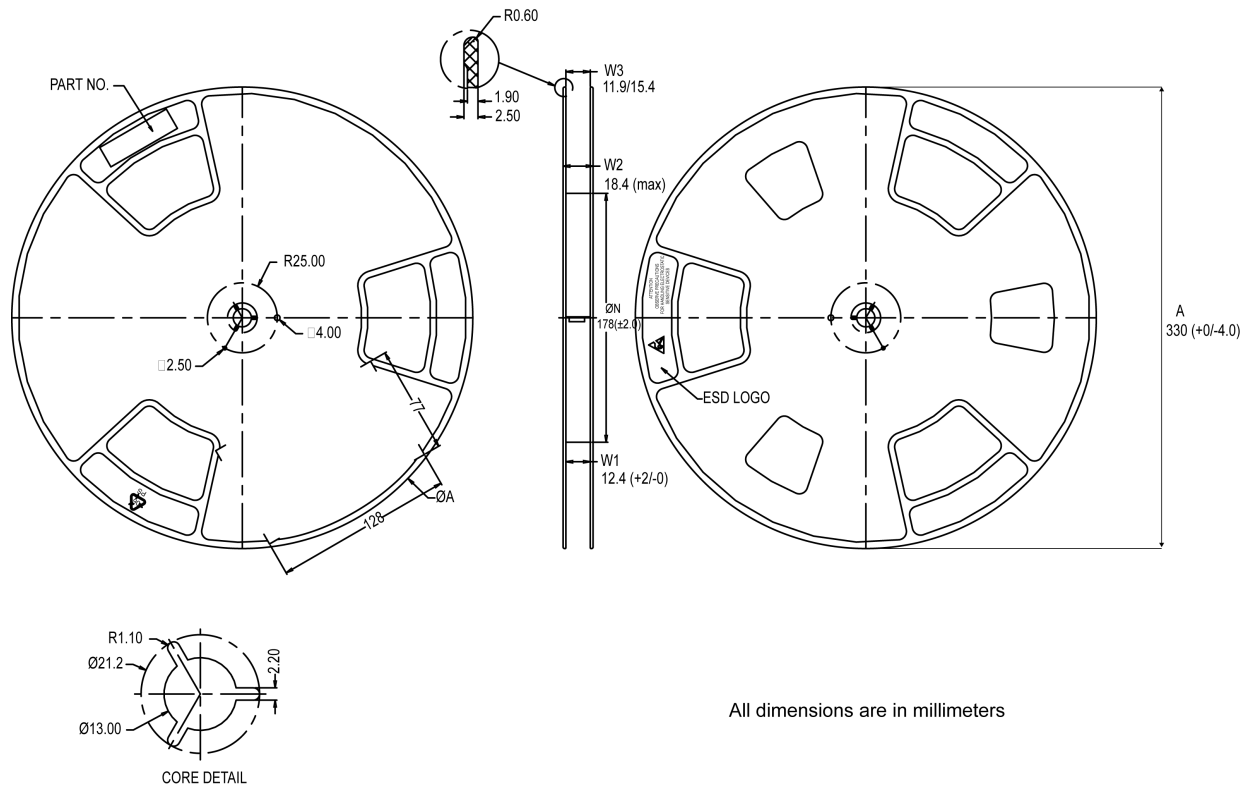


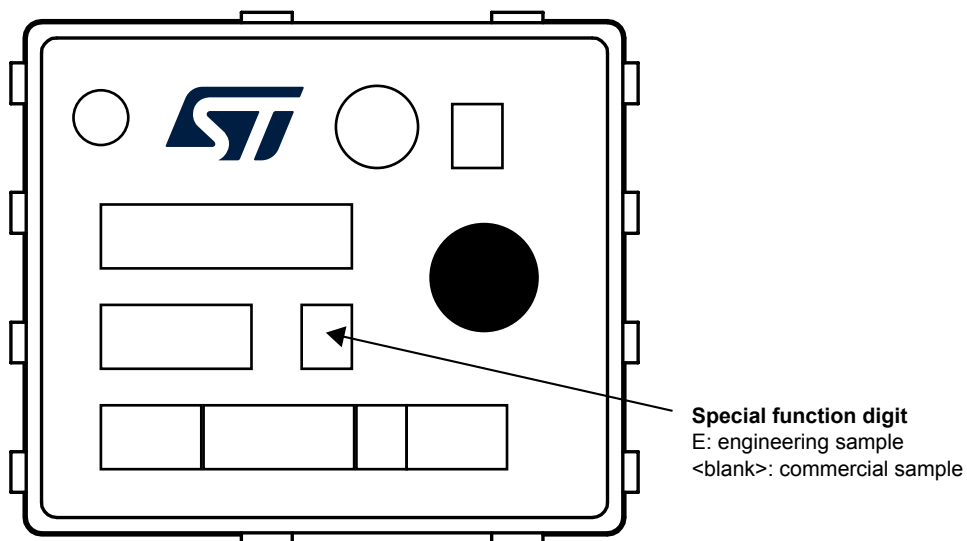
Figure 21. PowerFLAT 5x6 reel



8234350_Reel_rev_C

3.3 PowerFLAT 5x6 marking information

Figure 22. PowerFLAT 5x6 marking information



Note: *Engineering Samples: these samples can be clearly identified by a dedicated special symbol in the marking of each unit. These samples are intended to be used for electrical compatibility evaluation only; usage for any other purpose may be agreed only upon written authorization by ST. ST is not liable for any customer usage in production and/or in reliability qualification trials.*

Commercial Samples: fully qualified parts from ST standard production with no usage restrictions.

Revision history

Table 8. Document revision history

Date	Revision	Changes
27-Apr-2022	1	Initial release.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical characteristics (curves)	5
3	Package information	8
3.1	[Package name] package information	8
3.2	PowerFLAT 5x6 packing information	10
3.3	PowerFLAT 5x6 marking information	12
	Revision history	13
	Contents	14

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